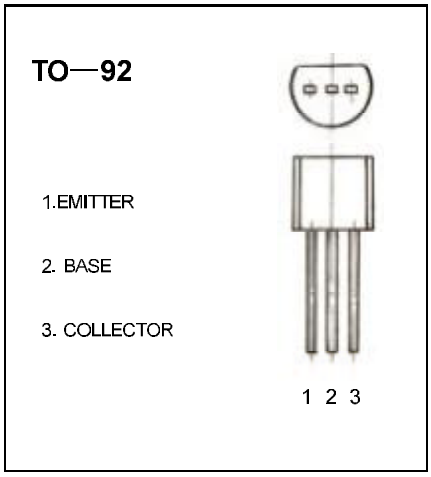
DONGGUAN NANJING ELECTRONICS LTD.,

# TO-92 Plastic-Encapsulate Transistors

## BC350 TRANSISTOR (PNP)




### FEATURES

Power dissipation

$P_{CM}$: 0.3 W（Tamb=25℃）

Collector current

$I_{CM}$: -0.1 A

Collector-base voltage

$V_{(BR)CBO}$ : -50 V

Operating and storage junction temperature range

$T_J$, $T_{stg}$: -55℃ to +150℃

### ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C$= -100μA， $I_E$=0 | -50 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C$= -1mA, IB=0 | -45 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E$= -100μA, $I_C$=0 | -5 | | | V |
| Collector cut-off current | $I_{CBO}$ | $V_{CB}$=-50V, $I_E$=0 | | | -0.1 | μA |
| Collector cut-off current | $I_{CEO}$ | $V_{CE}$=-35V, $I_B$=0 | | | -0.1 | μA |
| Emitter cut-off current | $I_{EBO}$ | $V_{EB}$= -3V, $I_C$=0 | | | -0.1 | μA |
| DC current gain | $h_{FE}$ | $V_{CE}$=-5 V, $I_C$= -2mA | 40 | | 450 | |
| Collector-emitter saturation voltage | $V_{CEsat}$ | $I_C$= -10mA, $I_B$= -1mA | | | -0.3 | V |
| Base-emitter saturation voltage | $V_{BEsat}$ | $I_C$= -10mA, $I_B$= -1mA | | | -1 | V |
| Transition frequency | $f_T$ | $V_{CE}$=-5V,$I_C$=-10mA, f=30MHz | 125 | | | MHz |

## Typical Characteristics

**BC350**

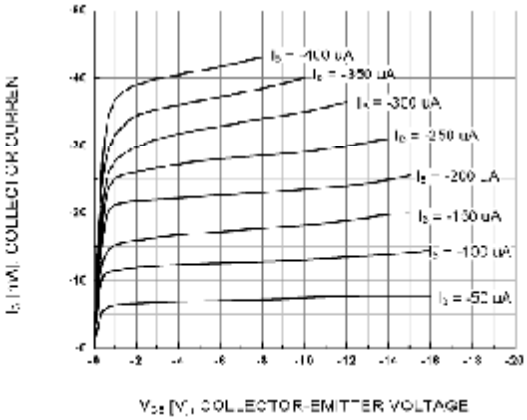



**Figure 1. Static Characteristic**

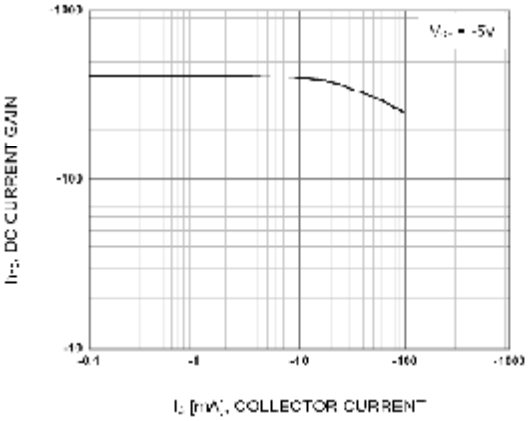



**Figure 2. DC current Gain**

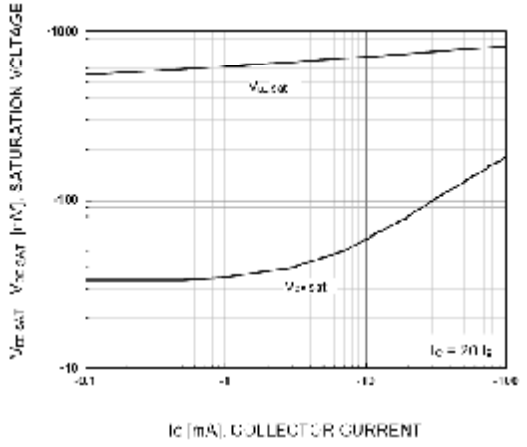



**Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage**

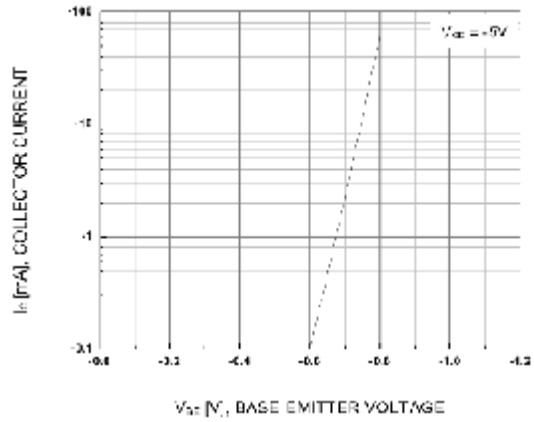



**Figure 4. Base-Emitter On Voltage**

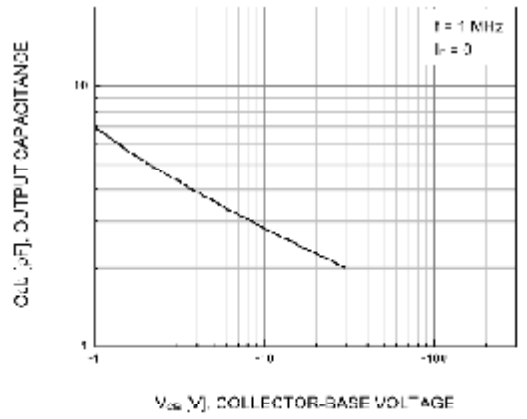



**Figure 5. Collector Output Capacitance**

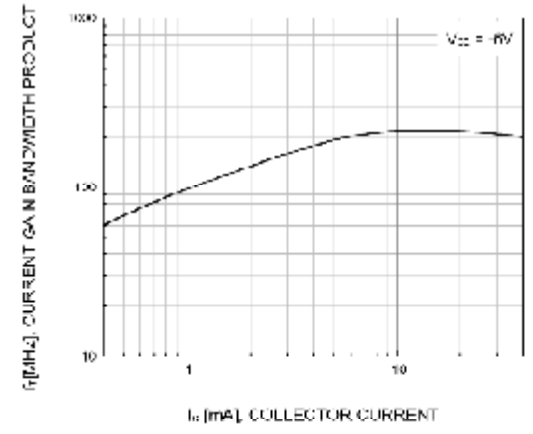



**Figure 6. Current Gian Bandwidth Product**